

## SMP3022-01ETG TVS Arrays

### Description

The SMP3022 includes back-to-back TVS diodes fabricated in a proprietary silicon avalanche technology to provide protection for electronic equipment that may experience destructive electrostatic discharges (ESD). These robust diodes can safely absorb repetitive ESD strikes up to the maximum level specified in the IEC61000-4-2 international standard ( $\pm 20\text{kV}$  contact discharge) without performance degradation. The back-to-back configuration provides symmetrical ESD protection for data lines when AC signals are present and the low loading capacitance makes it ideal for protecting high speed data lines such as HDMI, USB2.0, USB3.0 and eSATA.

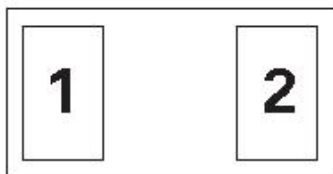
### Features

- ESD protection in accordance with:  
IEC 61000-4-2 (ESD)  $\pm 30\text{kV}$  (air),  $\pm 20\text{kV}$  (contact)  
IEC 61000-4-5 (lightning) 3A (8/20  $\mu\text{s}$ )  
IEC 61000-4-4 (EFT) 40A (5/50ns)
- Low capacitance of 0.35pF @ VR=0V (TYP)
- Low leakage current of 100nA at 5.3V(MAX)
- Extremely low dynamic resistance (0.7  $\Omega$  TYP)

### Applications

- USB 3.0/USB 2.0/MHL
- MIPI Camera and Display
- HDMI 2.0, DisplayPort 1.3, eSATA
- Set Top Boxes, Game Consoles
- Smart Phones
- External Storage
- Ultrabooks, Notebooks
- Tablets, eReaders
- High Speed Serial Interfaces

### Pinout



### Functional Block Diagram



## Ordering Information

| Device        | Package | Packaging Options              | P0/P1   | Packaging Specifications | Min. Order Qty. |
|---------------|---------|--------------------------------|---------|--------------------------|-----------------|
| SMP3022-01ETG | SOD882  | Tape & Reel - 8mm tape/7" reel | 4mm/2mm | EIA RS-481               | 10000           |

## Absolute Maximum Ratings @T<sub>A</sub>=25°C unless otherwise specified

| Parameter                      | Symbol          | Value        | Units |
|--------------------------------|-----------------|--------------|-------|
| Peak Pulse Current (tp=8/20µs) | I <sub>PP</sub> | 3.0          | A     |
| Operating Temperature          | T <sub>OP</sub> | -40 to + 125 | °C    |
| Peak Pulse Power (tP=8/20µs)   | P <sub>PK</sub> | 20           | W     |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

## Thermal Information

| Parameter                                   | Value        | Units |
|---|--------------|-------|
| Storage Temperature Range                   | -55 to + 150 | °C    |
| Maximum Junction Temperature                | 150          | °C    |
| Maximum Lead Temperature (Soldering 20-40s) | 260          | °C    |

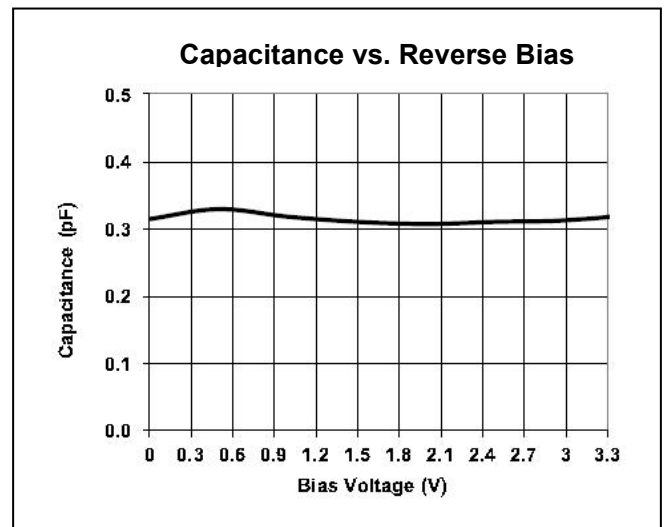
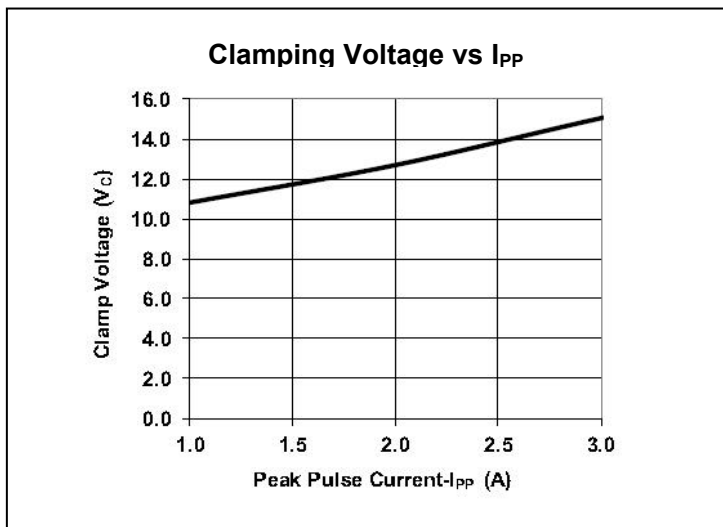
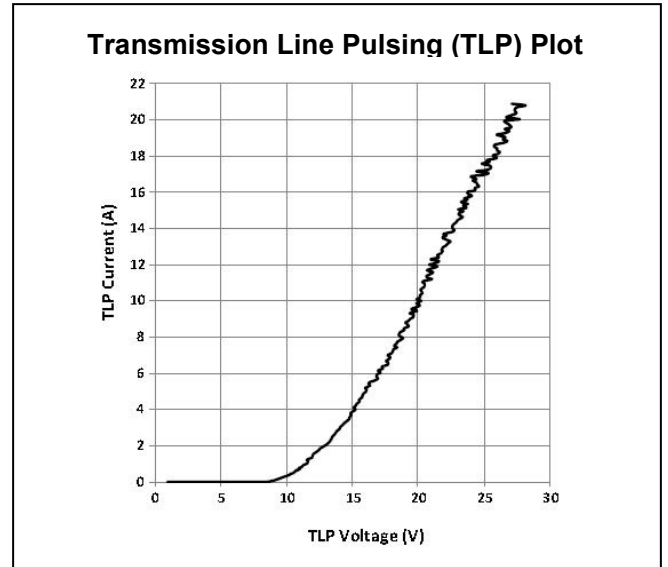
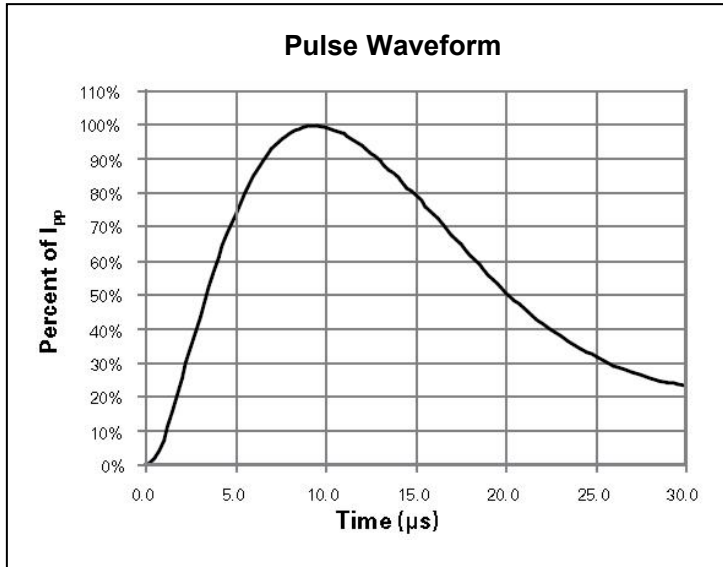
## Electrical Characteristics (T<sub>OP</sub>=25°C)

| Characteristics                     | Symbol            | Condition                            | Min. | Typ. | Max. | Units |
|-------------------------------------|-------------------|--------------------------------------|------|------|------|-------|
| Reverse Stand-Off Voltage           | V <sub>RWM</sub>  | -                                    | -    | -    | 5.3  | V     |
| Reverse Breakdown Voltage           | V <sub>BR</sub>   | I <sub>R</sub> =1mA                  | 6.8  | 7.8  | 9.0  | V     |
| Reverse Leakage Current             | I <sub>LEAK</sub> | V <sub>R</sub> =5.3V                 | -    | <10  | 100  | nA    |
| Clamping Voltage <sup>1</sup>       | V <sub>C</sub>    | I <sub>PP</sub> = 1A, tp=8/20µs, Fwd | -    | -    | 12.0 | V     |
| Dynamic Resistance <sup>2</sup>     | R <sub>DYN</sub>  | TLP, tp=100ns, I/O to GND            | -    | 0.7  | -    | Ω     |
| ESD With stand Voltage <sup>1</sup> | V <sub>ESD</sub>  | IEC61000-4-2 (Contact)               | ±20  | -    | -    | kV    |
|                                     |                   | IEC61000-4-2 (Air)                   | ±30  | -    | -    | kV    |
| Junction Capacitance <sup>1</sup>   | C <sub>D</sub>    | Reverse Bias=0V, f=1 MHz             | -    | 0.35 | 0.5  | pF    |

Note: 1 Parameter is guaranteed by design and/or device characterization.

2 Transmission Line Pulse (TLP) with 100ns width and 200ps rise time.

**Ratings and Characteristics Curves**



**Part Name Information**

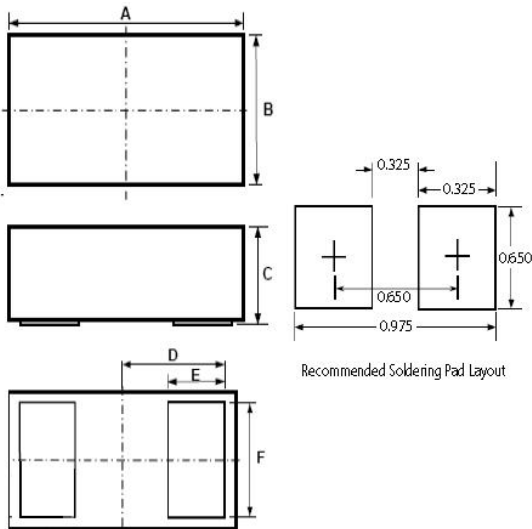
SMP 3022 - 01 E T G

- TVS Arrays Product
- Series
- Number of Channels
- Package E: SOD882
- T= Tape & Reel
- G= Green

**Marking Diagram**

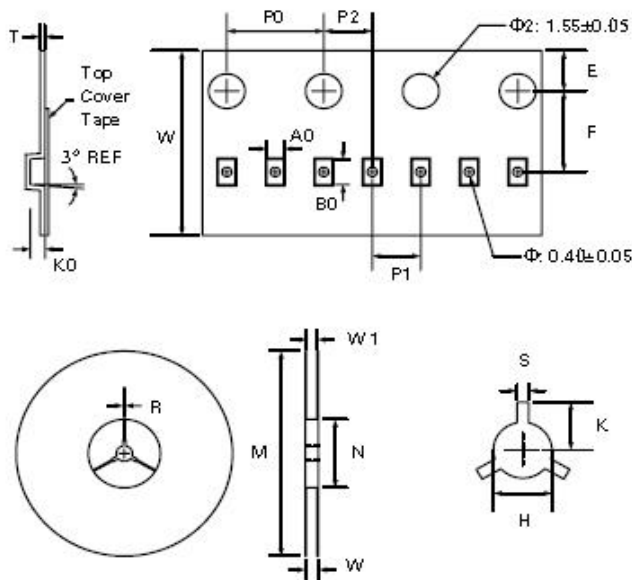


**Mechanical Dimensions SOD882**



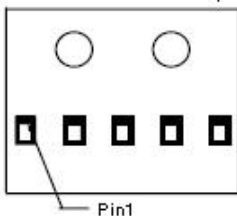
| Symbol   | Package     |      |      | SOD882 |       |       |
|----------|-------------|------|------|--------|-------|-------|
|          | JEDEC       |      |      | MO-236 |       |       |
|          | Millimeters |      |      | Inches |       |       |
|          | Min         | Typ  | Max  | Min    | Typ   | Max   |
| <b>A</b> | 0.90        | 1.00 | 1.10 | 0.037  | 0.039 | 0.041 |
| <b>B</b> | 0.50        | 0.60 | 0.70 | 0.022  | 0.024 | 0.026 |
| <b>C</b> | 0.40        | 0.50 | 0.60 | 0.016  | 0.020 | 0.024 |
| <b>D</b> | 0.45        |      |      | 0.018  |       |       |
| <b>E</b> | 0.20        | 0.25 | 0.35 | 0.008  | 0.010 | 0.012 |
| <b>F</b> | 0.45        | 0.50 | 0.55 | 0.018  | 0.020 | 0.022 |

**Embossed Carrier Tape & Reel Specification — SOD882**



| Symbol    | Tape Dimensions |      |
|-----------|-----------------|------|
|           | Millimeters     |      |
|           | Min             | Max  |
| <b>A0</b> | 0.65            | 0.75 |
| <b>B0</b> | 1.10            | 1.20 |
| <b>K0</b> | 0.50            | 0.60 |
| <b>E</b>  | 1.65            | 1.85 |
| <b>F</b>  | 3.45            | 3.55 |
| <b>P0</b> | 3.90            | 4.10 |
| <b>P1</b> | 1.90            | 2.10 |
| <b>P2</b> | 1.95            | 2.05 |
| <b>T</b>  | 1.95            | 2.05 |
| <b>W</b>  | 7.90            | 8.10 |

Device Orientation in Tape



| Symbol    | Reel Dimensions<br>(Size $\phi$ 178) |       |
|-----------|--------------------------------------|-------|
|           | Millimeters                          |       |
|           | Min                                  | Max   |
| <b>M</b>  | 177.0                                | 179.0 |
| <b>N</b>  | 59.0                                 | 61.0  |
| <b>W</b>  | 11.0                                 | 12.0  |
| <b>W1</b> | 8.5                                  | 9.5   |
| <b>H</b>  | 12.5                                 | 13.5  |
| <b>S</b>  | 1.9                                  | 2.1   |
| <b>K</b>  | 10.8                                 | 11.2  |
| <b>R</b>  | 0.95                                 | 1.05  |

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